



SUM52N20-39P-E3 Information



For Reference Only

Part Number SUM52N20-39P-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single MOSFET N-CH 200V 52A D2PAK

Description MOSFET N-CH 200V 52A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SUM52N20-39P-E3 Specifications

Manufacturer Part NumberSUM52N20-39P-E3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsPackageTo-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C52A (Tc)Drive Voltage (Max Rds On, Min Rds On)10V, 15VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs185nC @ 15VInput Capacitance (Ciss) (Max) @ Vds4220pF @ 25VVgs (Max)±25VFET Feature-
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FET Feature -
Power Dissipation (Max) 3.12W (Ta), 250W (Tc)
Rds On (Max) @ Id, Vgs 38 mOhm @ 20A, 15V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Surface Mount
Supplier Device Package TO-263 (D2Pak)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
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SUM52N20-39P-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SUM52N20-39P-E3 Payment Methods



















SUM52N20-39P-E3 Shipping Methods













If you have any question about SUM52N20-39P-E3, please do not hesitate to contact us!

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